

WHAT IS CLAIMED IS:

1. A semiconductor device having a test mark comprising:
 a semiconductor substrate;
 a first TEOS layer formed on said semiconductor
 5 substrate;
 a second TEOS layer formed on said first TEOS layer
 and having a lower fluidity than that of said first TEOS
 layer at an elevated temperature;
 a recess formed in said first and second TEOS layers
 10 and exposing the surface of said semiconductor substrate,
 wherein the horizontal cross section of said recess is
 substantially rectangular in configuration; and
 a metal layer formed on said first TEOS layer and
 opposing to the corner of said recess.
- 15 2. A semiconductor device according to claim 1, wherein
 said first TEOS layer contains boron and/or phosphorus.
3. A semiconductor device according to claim 1, wherein
 said metal layer is a square-shaped layer surrounding said
 recess.
- 20 4. A semiconductor device according to claim 1, wherein
 said metal layer is an L-shaped layer surrounding the
 corner of said recess.
5. A semiconductor device according to claim 1, wherein
 said metal layer is a delta-shaped layer of which one side
 25 opposes to the corner of said recess.

6. A semiconductor device according to claim 1, further comprising an outer metal layer formed outside of said metal layer so that said outer metal layer opposes to the corner of said recess through said metal layer.
- 5 7. A semiconductor device according to claim 1, wherein a lower metal layer is embedded in said first TEOS layer which extends between the top and bottom surfaces each neighboring to said semiconductor substrate and said metal layer.
- 10 8. A semiconductor device according to claim 7, wherein said lower metal layer consists of a plurality of cylindrical metal layers.

2025 RELEASE UNDER E.O. 14176